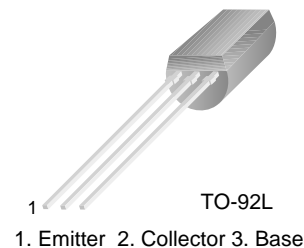


■■ APPLICATION: Low Frequency Power Amplifier Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CBO</sub>	25	V
Collector-emitter voltage	V <sub>CEO</sub>	20	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	1	A
Collector Power Dissipation	P <sub>C</sub>	900	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	85		320		V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA
Collector Cut-off Current	I <sub>CBO</sub>			1	μA	V <sub>CB</sub> = 20V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			0.1	μA	V <sub>EB</sub> = 3V, I <sub>C</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	25			V	I <sub>C</sub> = 0.1mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	20			V	I <sub>C</sub> = 1mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5			V	I <sub>E</sub> = 0.1mA, I <sub>C</sub> =0
Base-Emitter Voltage	V <sub>BE</sub>		0.79	1	V	V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			0.5	V	I <sub>C</sub> = 800mA, I <sub>B</sub> = 80mA
Gain bandwidth product	f <sub>T</sub>	150	190		MHz	I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2V
Common Base Output Capacitance	C <sub>ob</sub>		22		PF	V <sub>CB</sub> = 10V, I <sub>E</sub> =0, f = 1MHz

■■ h<sub>FE</sub> Classification And Marking

Classification	B	C	D
h <sub>FE</sub>	85~170	120~240	200~320